



February 1990

F100322 Low Power 9-Bit Buffer

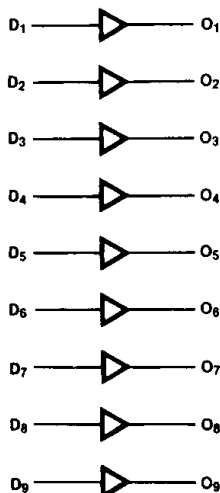
General Description

The F100322 is a monolithic 9-bit buffer. The device contains nine non-inverting buffer gates with single input and output. All inputs have 50 kΩ pull-down resistors and all outputs are buffered.

Features:

- 30% power reduction of the F100122
- 2000V ESD protection
- Pin/function compatible with F100122
- Voltage compensated operating range = -4.2V to -5.7V

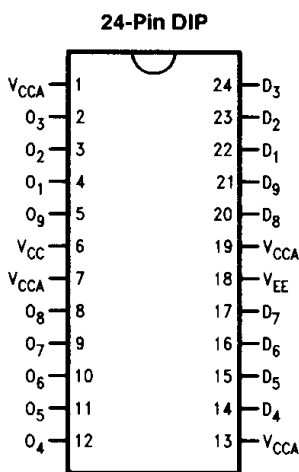
Logic Symbol



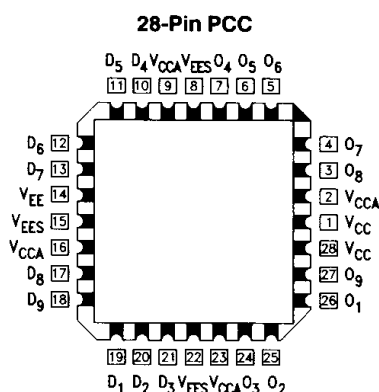
Pin Names	Description
D ₁ , D ₉	Data Inputs
O ₁ , O ₉	Data Outputs

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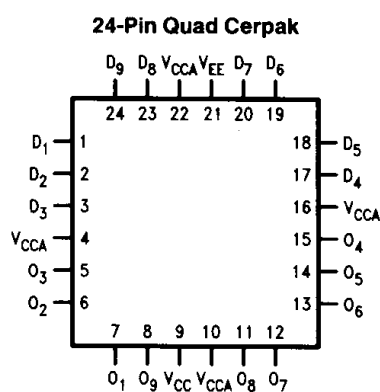
Connection Diagrams



TL/F/10608-2



TL/F/10608-4



TL/F/10608-3

F100322 Low Power 9-Bit Buffer

Absolute Maximum Ratings

Above which the useful life may be impaired. (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature (T _{STG})	-65°C to +150°C
Maximum Junction Temperature (T _J)	
Ceramic	+175°C
Plastic	+150°C
V _{EE} Pin Potential to Ground Pin	-7.0V to +0.5V
Input Voltage (DC)	V _{EE} to +0.5V

Output Current (DC Output HIGH)	-50 mA
ESD (Note 2)	≥2000V

Recommended Operating Conditions

Case Temperature (T _C)	
Commercial	0°C to +85°C
Military	-55°C to +125°C
Supply Voltage (V _{EE})	
Commercial	-5.7V to -4.2V
Military	-5.7V to -4.2V

Commercial Version

DC Electrical Characteristics

V_{EE} = -4.2V to -5.7V, V_{CC} = V_{CCA} = GND, T_C = 0°C to +85°C (Note 3)

Symbol	Parameter	Min	Typ	Max	Units	Conditions	
V _{OH}	Output HIGH Voltage	-1025	-955	-870	mV	V _{IN} = V _{IH} (Max) or V _{IL} (Min)	Loading with 50Ω to -2.0V
V _{OL}	Output LOW Voltage	-1830	-1705	-1620			
V _{OHC}	Output HIGH Voltage	-1035			mV	V _{IN} = V _{IH} (Min) or V _{IL} (Max)	Loading with 50Ω to -2.0V
V _{OLC}	Output LOW Voltage			-1610			
V _{IH}	Input HIGH Voltage	-1165		-870	mV	Guaranteed HIGH Signal for All Inputs	
V _{IL}	Input LOW Voltage	-1830		-1475	mV	Guaranteed LOW Signal for All Inputs	
I _{IL}	Input LOW Current	0.50			μA	V _{IN} = V _{IL} (Min)	
I _{IH}	Input HIGH Current			240	μA	V _{IN} = V _{IH} (Max)	
I _{EE}	Power Supply Current	-65		-30	mA	Inputs Open	

Note 1: Absolute maximum ratings are those values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: ESD testing conforms to MIL-STD-883, Method 3015.

Note 3: The specified limits represent the "worst case" value for the parameter. Since these values normally occur at the temperature extremes, additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under "worst case" conditions.

Ceramic Dual-In-Line Package AC Electrical Characteristics

V_{EE} = -4.2V to -5.7V, V_{CC} = V_{CCA} = GND

Symbol	Parameter	T _C = 0°C		T _C = +25°C		T _C = +85°C		Units	Conditions
		Min	Max	Min	Max	Min	Max		
t _{PLH} t _{PHL}	Propagation Delay Data to Output	0.45	1.45	0.45	1.45	0.45	1.55	ns	Figures 1 and 2 (Note 1)
t _{TLH} t _{THL}	Transition Time 20% to 80%, 80% to 20%	0.35	1.20	0.35	1.20	0.35	1.20	ns	Figures 1 and 2

Note 1: The propagation delay specified is for single output switching. Delays may vary up to 200 ps with multiple outputs switching.

PCC and Cerpak AC Electrical Characteristics

V_{EE} = -4.2V to -5.7V, V_{CC} = V_{CCA} = GND

Symbol	Parameter	T _C = 0°C		T _C = +25°C		T _C = +85°C		Units	Conditions
		Min	Max	Min	Max	Min	Max		
t _{PLH} t _{PHL}	Propagation Delay Data to Output	0.45	1.25	0.45	1.25	0.45	1.35	ns	Figures 1 and 2 (Note 2)
t _{TLH} t _{THL}	Transition Time 20% to 80%, 80% to 20%	0.35	1.10	0.35	1.10	0.35	1.10	ns	Figures 1 and 2
t _{S,G-G}	Skew, Gate to Gate		TBD		TBD		TBD	ps	PCC Only (Note 1)

Note 1: Gate to gate skew is defined as the difference in propagation delays between each of the outputs.

Note 2: The propagation delay specified is for single output switching. Delays may vary up to 200 ps with multiple outputs switching.

Military Version—Preliminary DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$, $T_C = 0^\circ C$ to $+85^\circ C$

Symbol	Parameter	Min	Max	Units	T_C	Conditions		Notes
V_{OH}	Output HIGH Voltage	-1025	-870	mV	$0^\circ C$ to $+125^\circ C$	$V_{IN} = V_{IH} (Max)$ or $V_{IL} (Min)$	Loading with 50Ω to $-2.0V$	1, 2, 3
		-1085	-870	mV	$-55^\circ C$			
V_{OL}	Output LOW Voltage	-1830	-1620	mV	$0^\circ C$ to $+125^\circ C$	$V_{IN} = V_{IH} (Max)$ or $V_{IL} (Min)$	Loading with 50Ω to $-2.0V$	1, 2, 3
		-1830	-1555	mV	$-55^\circ C$			
V_{OHC}	Output HIGH Voltage	-1035		mV	$0^\circ C$ to $+125^\circ C$	$V_{IN} = V_{IH} (Max)$ or $V_{IL} (Min)$	Loading with 50Ω to $-2.0V$	1, 2, 3
		-1085		mV	$-55^\circ C$			
V_{OLC}	Output LOW Voltage		-1610	mV	$0^\circ C$ to $+125^\circ C$	$V_{IN} = V_{IH} (Max)$ or $V_{IL} (Min)$	Loading with 50Ω to $-2.0V$	1, 2, 3
			-1555	mV	$-55^\circ C$			
V_{IH}	Input HIGH Voltage	-1165	-870	mV	$-55^\circ C$ to $+125^\circ C$	Guaranteed HIGH Signal for All Inputs		1, 2, 3, 4
V_{IL}	Input HIGH Voltage	-1830	-1475	mV	$-55^\circ C$ to $+125^\circ C$	Guaranteed LOW Signal for All Inputs		1, 2, 3, 4
I_{IL}	Input LOW Current	0.50		μA	$-55^\circ C$ to $+125^\circ$	$V_{EE} = -4.2V$ $V_{IN} = V_{IL} (Min)$		1, 2, 3
I_{IH}	Input HIGH Current		240	μA	$0^\circ C$ to $+125^\circ C$	$V_{EE} = -5.7V$ $V_{IN} = V_{IH} (Max)$		1, 2, 3
			340	μA	$-55^\circ C$			
I_{EE}	Power Supply Current	-70	-25	mA	$-55^\circ C$ to $+125^\circ C$	Inputs Open		1, 2, 3

Note 1: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals $-55^\circ C$), then testing immediately without allowing for the junction temperature to stabilize due to heat dissipation after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 2: Screen tested 100% on each device at $-55^\circ C$, $+25^\circ C$, and $+125^\circ C$, Subgroups 1, 2, 3, 7, and 8.

Note 3: Sample tested (Method 5005, Table I) on each manufactured lot at $-55^\circ C$, $+25^\circ C$, and $+125^\circ C$, Subgroups A1, 2, 3, 7, and 8.

Note 4: Guaranteed by applying specified input condition and testing V_{OH}/V_{OL} .

Ceramic Dual-In-Line Package AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$

Symbol	Parameter	$T_C = -55^\circ C$		$T_C = +25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PLH} t_{PHL}	Propagation Delay Data to Output	0.30	1.80	0.40	1.60	0.40	1.80	ns	Figures 1 and 2	1, 2, 3, 5
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.30	1.20	0.30	1.20	0.30	1.20	ns		4

Cerpak AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$

Symbol	Parameter	$T_C = -55^\circ C$		$T_C = +25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PLH} t_{PHL}	Propagation Delay Data to Output	0.30	1.80	0.40	1.60	0.40	1.80	ns	Figures 1 and 2	1, 2, 3, 5
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.30	1.20	0.30	1.20	0.30	1.20	ns		4

Note 1: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals $-55^\circ C$), then testing immediately after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 2: Screen tested 100% on each device at $+25^\circ C$, only Subgroup A9.

Note 3: Sample tested (Method 5005, Table I) on each manufactured lot at $+25^\circ C$, Subgroup A9, and at $+125^\circ C$ and $-55^\circ C$ temperatures, Subgroups A10 and A11.

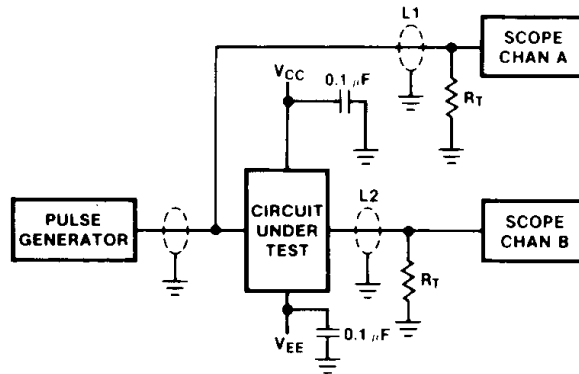
Note 4: Not tested at $+25^\circ C$, $+125^\circ C$, and $-55^\circ C$ temperature (design characterization data).

Note 5: The propagation delay specified is for single output switching. Delays may vary up to 200 ps with multiple outputs switching.

Test Circuit

Notes:

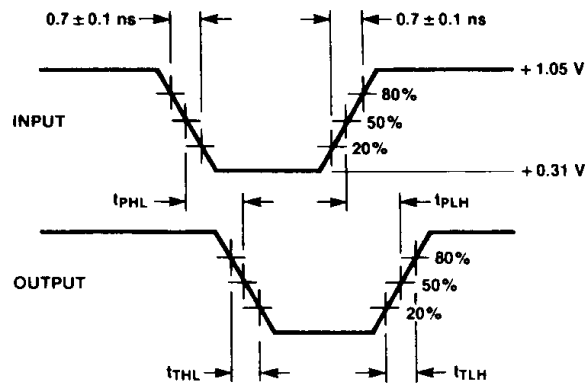
$V_{CC}, V_{CCA} = +2V, V_{EE} = -2.5V$
 $L1$ and $L2$ = equal length 50Ω impedance lines
 $R_T = 50\Omega$ terminator internal to scope
 Decoupling $0.1 \mu F$ from GND to V_{CC} and V_{EE}
 All unused outputs are loaded with 50Ω to GND
 C_L = Fixture and stray capacitance ≤ 3 pF



TL/F/10608-5

FIGURE 1. AC Test Circuit

Switching Waveforms

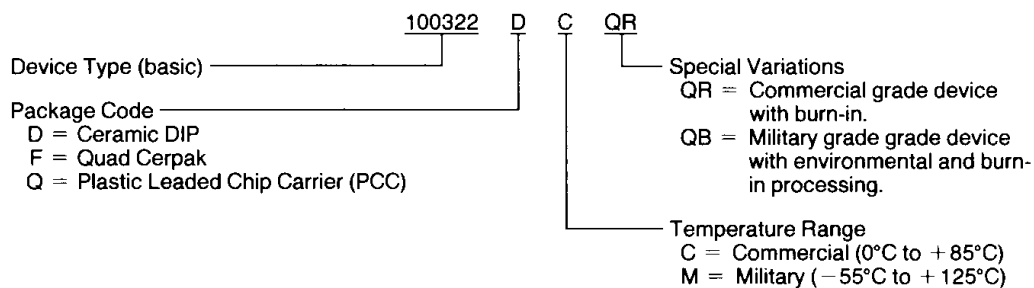


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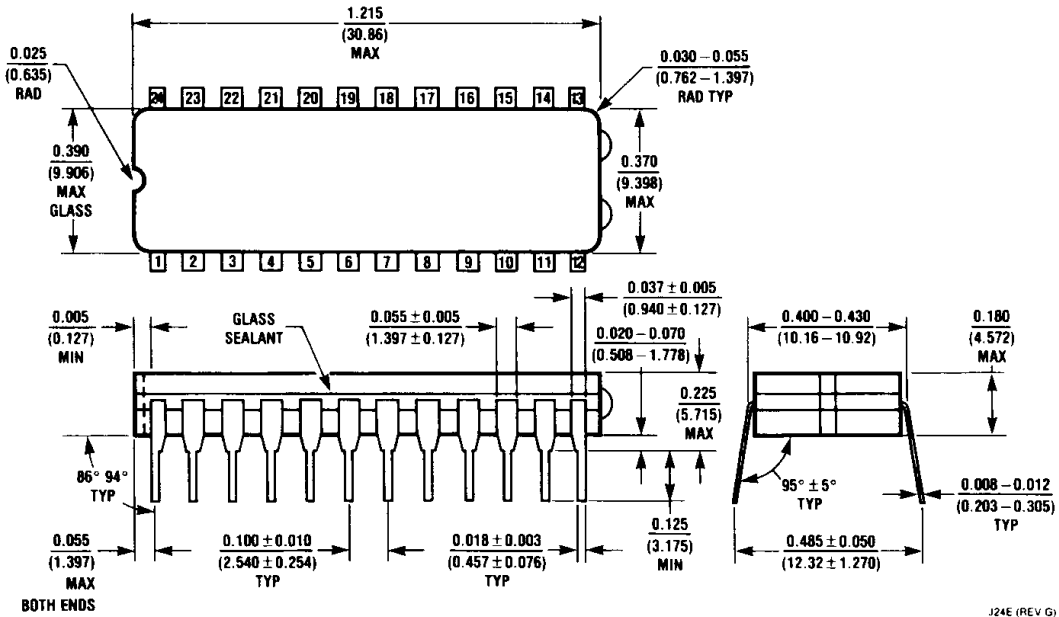
FIGURE 2. Propagation Delay and Transition Times

Ordering Information

The device number is used to form part of a simplified purchasing code where a package type and temperature range are defined as follows:

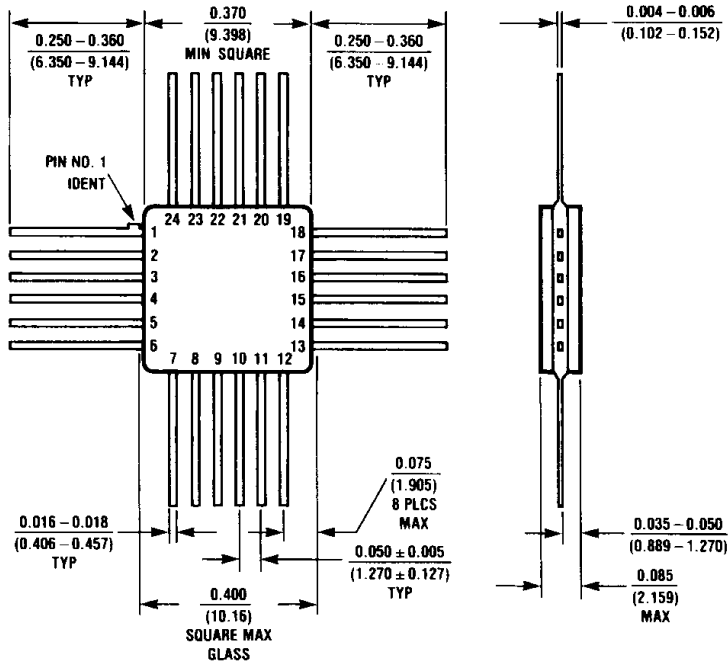


Physical Dimensions inches (millimeters)



24-Lead Ceramic Dual-In-Line Package (0.400" Wide) (D)
NS Package Number J24E

J24E (REV G)

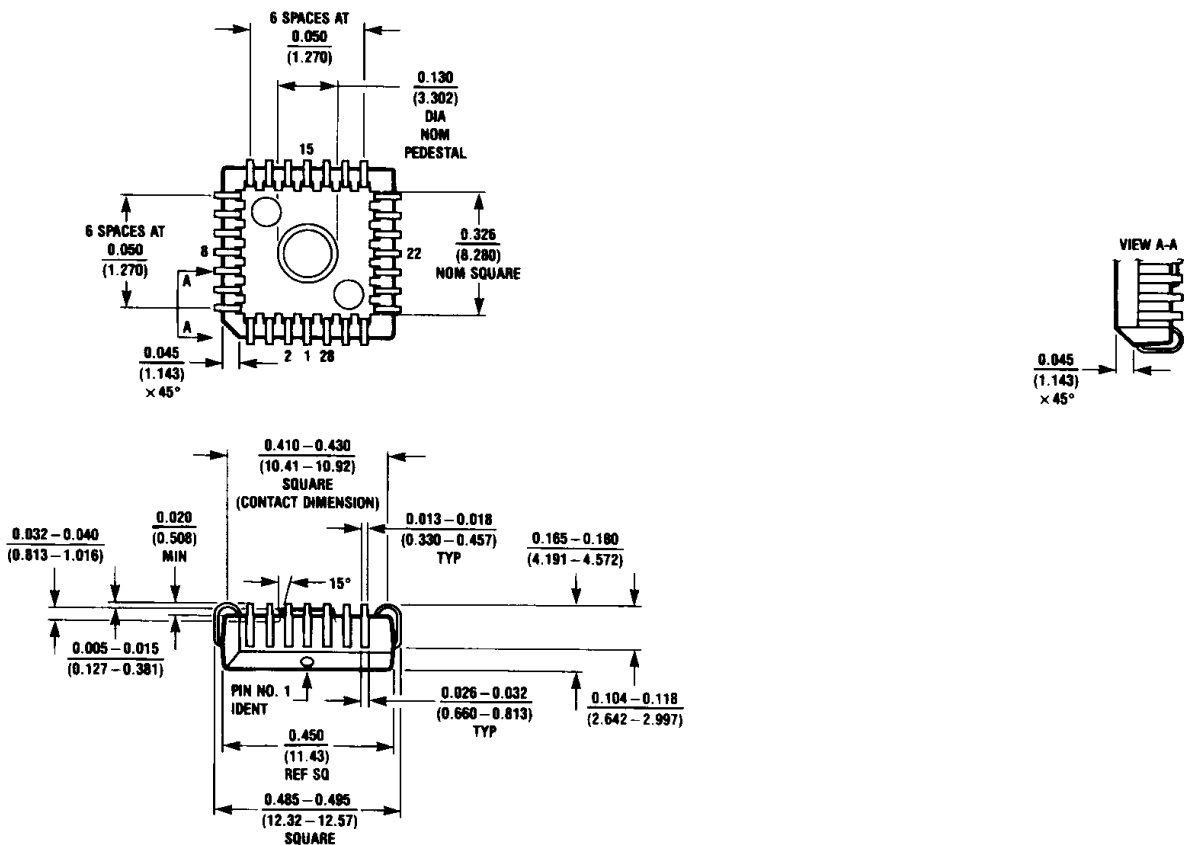


24-Lead Ceramic Flatpak (F)
NS Package Number W24B

W24B (REV C)

Physical Dimensions inches (millimeters) (Continued)

Lit. # 114907



**28-Lead Plastic Chip Carrier (Q)
NS Package Number V28A**

V28A (REV G)

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